ME8107/ME8107-G

P-Channel Enhancement Mode MOSFET, ESD Protected

GENERAL DESCRIPTION

The ME8107 is the P-Channel logic enhancement mode power field effect transistors are produced using high cell density, DMOS trench technology. This high density process is especially tailored to minimize on-state resistance. These devices are particularly suited for low voltage application such as cellular phone and notebook computer power management and other battery powered circuits where high-side switching and low in-line power loss are needed in a very small outline surface mount package.

FEATURES

- $R_{DS(ON)} \leqq 7.2m\Omega @ V_{GS}=-10V$
- $R_{DS(ON)} \leqq 12m\Omega @ V_{GS}=-4.5V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability

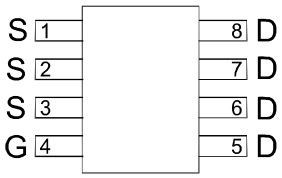
APPLICATIONS

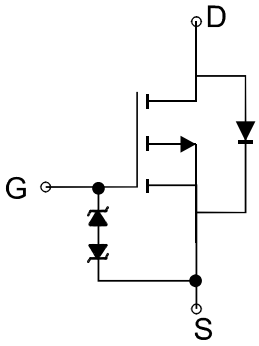
- Power Management in Note book
- Portable Equipment
- Battery Powered System
- DC/DC Converter
- Load Switch
- LCD Display inverter

PIN CONFIGURATION

(SOP-8)

Top View





Ordering Information: ME8107(Pb-free)

ME8107-G (Green product-Halogen free)

Absolute Maximum Ratings (T_A=25℃ Unless Otherwise Noted)

Parameter		Symbol	Maximum Ratings	Unit
Drain-Source Voltage		V_{DS}	-35	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_A=25℃	I_D	-13	A
	T_A=70℃		-10	
Pulsed Drain Current		I_{DM}	-52	A
Maximum Power Dissipation*	T_A=25℃	P_D	2	W
	T_A=70℃		1.3	
Operating Junction Temperature		T_J	-55 to 150	℃
Thermal Resistance-Junction to Ambient*		$R_{\theta JA}$	62.5	℃/W

* The device mounted on 1in^2 FR4 board with 2 oz copper

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Electrical Characteristics (T_A=25℃ Unless Otherwise Specified)

Symbol	Parameter	Limit	Min	Typ	Max	Unit
STATIC						
$V_{BR(DSS)}$	Drain-source breakdown voltage	I_D=-10mA, V_{GS}=0V	-35			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}= V_{DS}, I_D=-250μA	-1		-3.0	V
I_{GSS}	Gate Leakage Current	V_{DS}=0V, V_{GS}=±16V			±10	μA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-30V, V_{GS}=0V			-10	μA
$R_{DS(ON)}$	Drain-Source On-State Resistance[a]	V_{GS}=-10V, I_D= -7A		5.5	7.2	mΩ
		V_{GS}=-4.5V, I_D= -6.5A		8	12	
V_{SD}	Diode Forward Voltage	I_{DR}=-7A, V_{GS}=0V		0.78		V
DYNAMIC						
Qg	Total Gate Charge	V_{DD}=-24V, V_{GS}=-4.5V, I_D=-13A		58		nC
Qg	Total Gate Charge	V_{DD}=-24V, V_{GS}=-10V, I_D=-13A		120		
Qgs	Gate-Source Charge			26		
Qgd	Gate-Drain Charge			33		
$t_{d(on)}$	Turn-On Delay Time	V_{DD}=-15V, R_L =15Ω V_{GS}=-10V,R_G=6Ω		77		ns
t_r	Turn-On Rise Time			32		
$t_{d(off)}$	Turn-Off Delay Time			213		
t_f	Turn-Off Fall Time			64		
Ciss	Input Capacitance	V_{DS}=-15V, V_{GS}=0V, f=-1MHZ		5330		pF
Coss	Output Capacitance			710		
Crss	Reverse Transfer Capacitance			242		

Notes: a. Pulse test: pulse width≦ 300us, duty cycle≦ 2%, Guaranteed by design, not subject to production testing.

b. Matsuki Electric/ Force mos reserves the right to improve product design, functions and reliability without notice.

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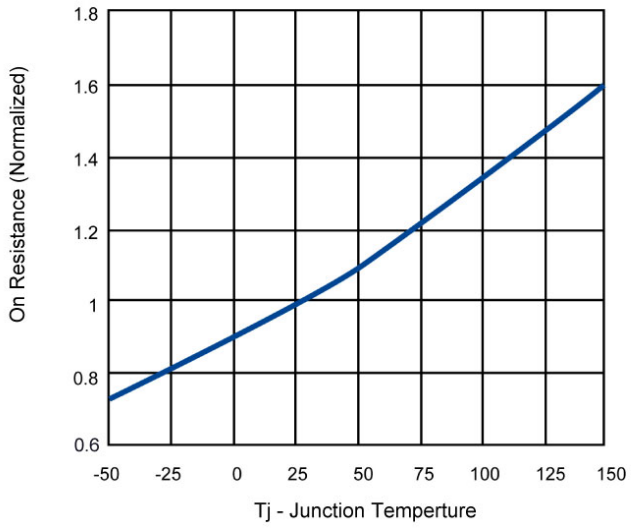
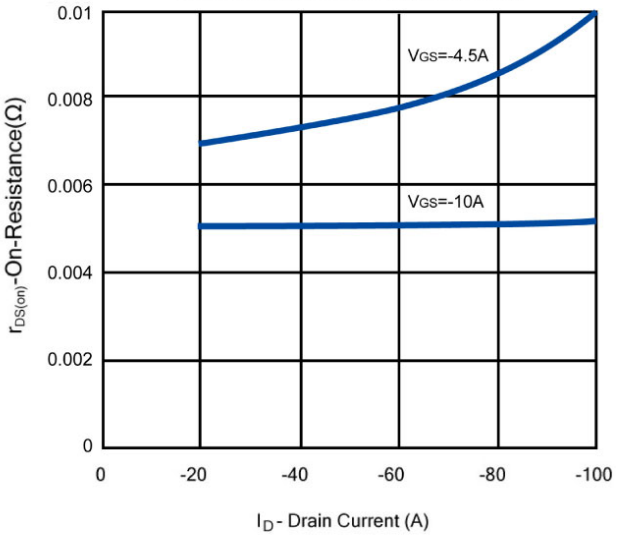
Typical Characteristics (T_J =25℃ Noted)

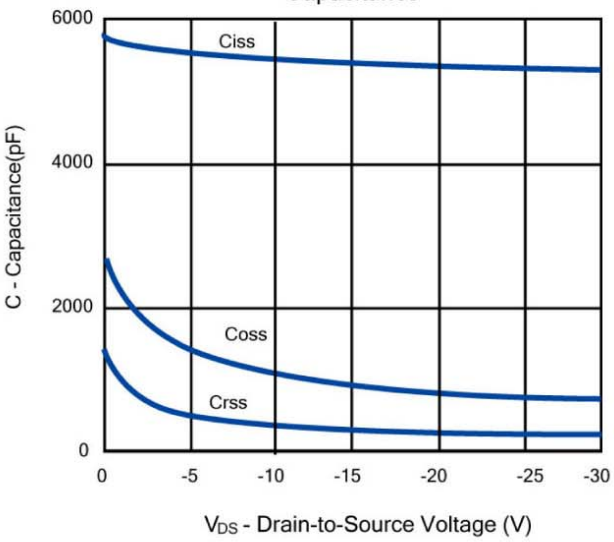
On Resistance vs. Junction Temperture



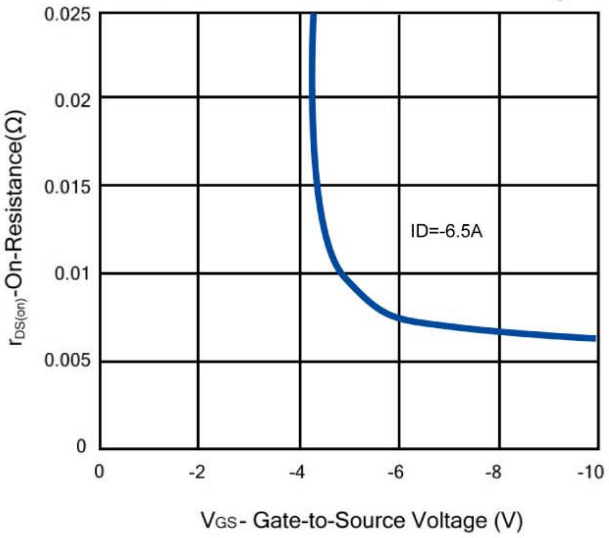
On-Resistance vs. Drain Current



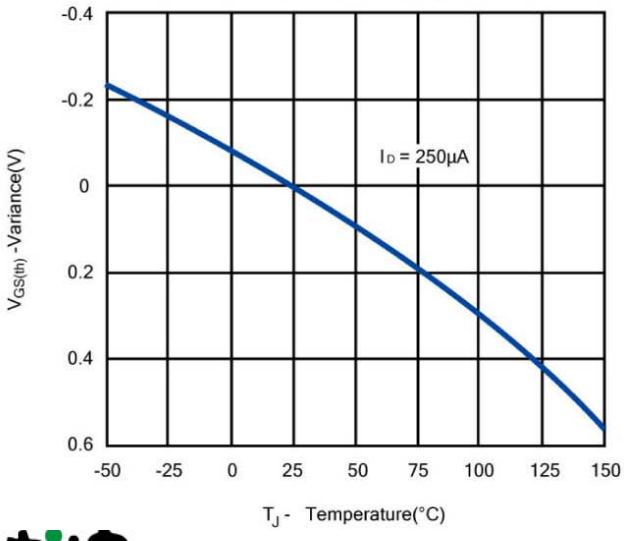
Capacitance



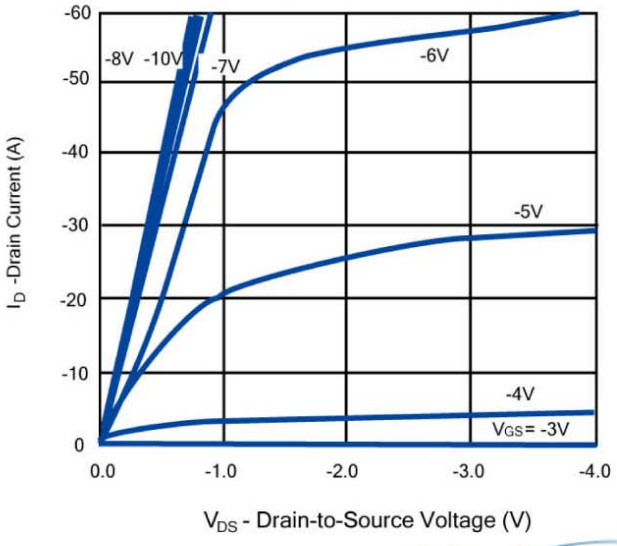
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



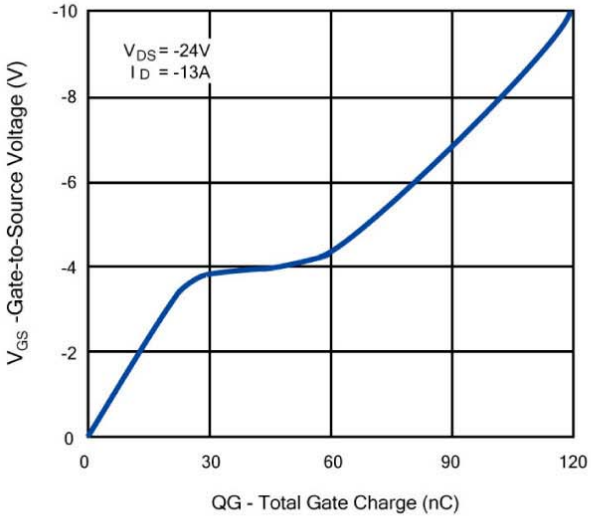
On-Region Characteristics



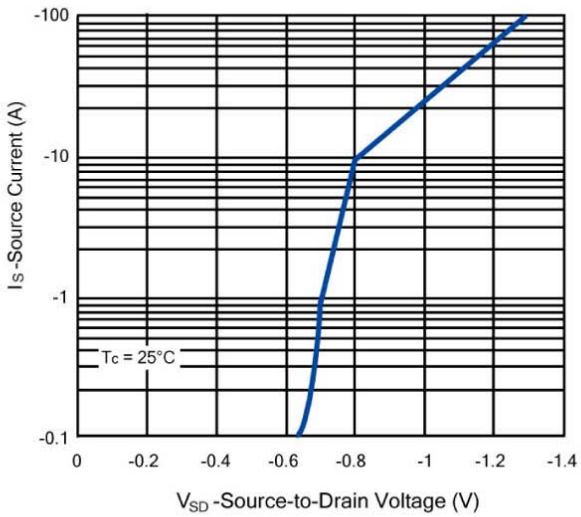
P-Channel Enhancement Mode MOSFET, ESD Protected

Typical Characteristics (T_J =25℃ Noted)

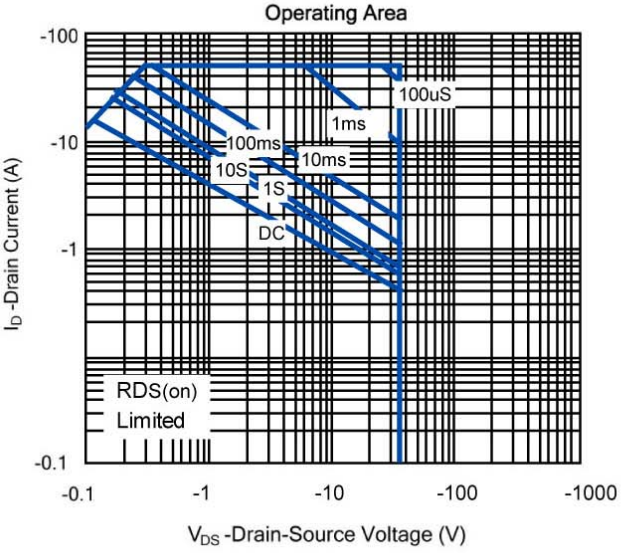
Gate Charge



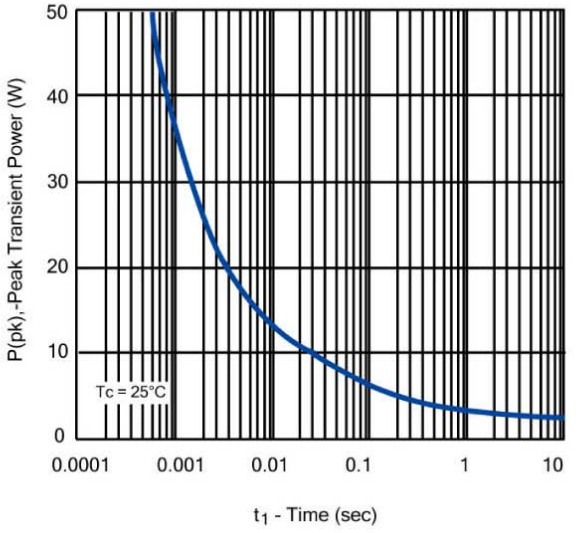
Body-diode characteristics



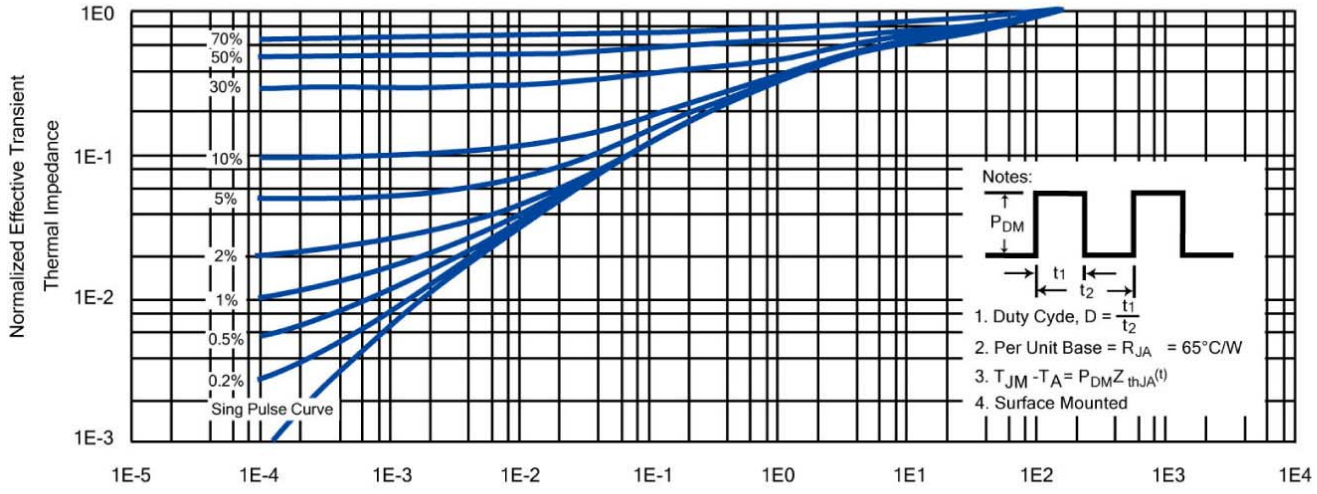
Maximum Forward Biased Safe Operating Area



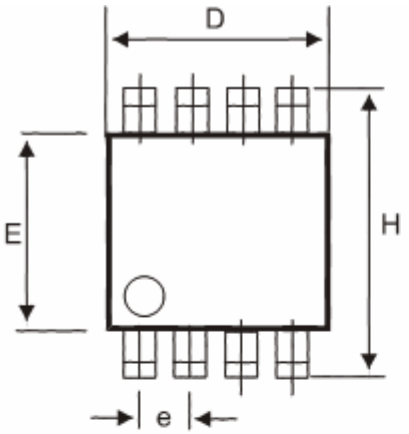
Single Pulse Maximum Power Dissipation

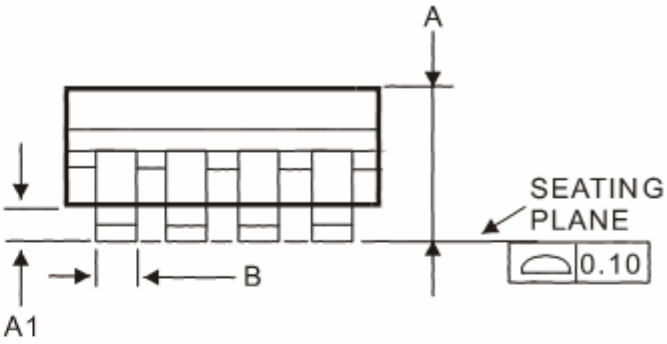


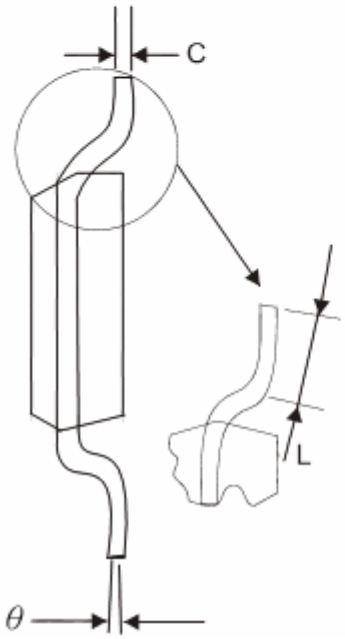
Normalized Thermal Transient Impedance, Junction-to-Ambient



SOP-8 Package Outline







DIM	MILLIMETERS (mm)	
	MIN	MAX
A	1.35	1.75
A1	0.10	0.25
B	0.35	0.49
C	0.18	0.25
D	4.80	5.00
E	3.80	4.00
e	1.27 BSC	
H	5.80	6.20
L	0.40	1.25
θ	0°	7°

Note: 1. Refer to JEDEC MS-012AA.

2. Dimension “D” does not include mold flash, protrusions or gate burrs . Mold flash, protrusions or gate burrs shall not exceed 0.15 mm per side.